

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

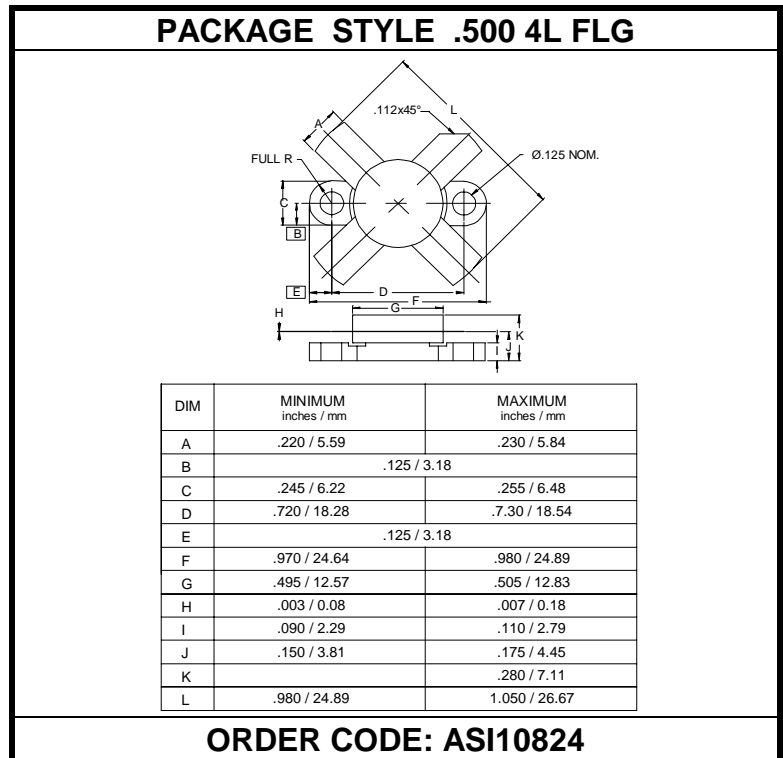
The **ASI MRF421** is Designed for High linear amplifier applications from 2.0 to 30 MHz.

FEATURES:

- $P_G = 12$ dB min. at 100 W/30 MHz
- $IMD_3 = -30$ dBc max. at 100 W(PEP)
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	20 A
V_{CBO}	45 V
V_{CEO}	20 V
V_{EBO}	3.0 V
P_{DISS}	290 W @ $T_C = 25$ °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	0.6 °C/W


CHARACTERISTICS $T_C = 25$ °C

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 50$ mA		20			V
BV_{CES}	$I_C = 100$ mA		45			V
BV_{CBO}	$I_C = 100$ mA		45			V
BV_{EBO}	$I_E = 10$ mA		4.0			V
I_{CES}	$V_{CE} = 16$ V				10	mA
h_{FE}	$V_{CE} = 5.0$ V	$I_C = 5.0$ A	10		200	---
C_{OB}	$V_{CB} = 12.5$ V	$f = 1.0$ MHz		650		pF
G_P	$V_{CE} = 12.5$ V	$I_{CQ} = 150$ mA	10	12		dB
IMD_3	$V_{CE} = 12.5$ V	$I_{CQ} = 150$ mA			-30	dBc
η_C		$P_{OUT} = 100$ W	40			%